IN THE ABSTRACT:

Please cancel the current abstract and insert the following.

~~An exposure apparatus has an illuminating optical system for illuminating a mask with illuminating light from a light source, a projection optical system for projecting a pattern image, which has been formed on the mask, onto a wafer constituting a photosensitive substrate, and an alignment sensor constructing a position detection system for detecting an alignment mark on the wafer. The pattern region on the wafer is formed at a position offset toward the side of the alignment sensor from the projection center of the projection optical system, and the alignment sensor is disposed on the side near the pattern region formed on the wafer off-centered from the optic axis. By thus shortening baseline distance, the effects of measurement error due to baseline fluctuation can be reduced and it is possible to achieve highly precise detection of the position of an object to be detected (a position detection mark) and highly precise alignment.~~

-- An exposure apparatus includes a projection optical system for projecting a pattern, which has been formed on a reticle, onto a photosensitive substrate, wherein a projection region of the pattern, which region is formed on the substrate via the projection optical system, is formed at a position that is off-centered with respect to an optical axis of the projection optical system, a substrate stage capable of holding and moving the substrate, a substrate transport system for transporting the substrate to the substrate stage, wherein the substrate transport system is disposed on the side of the projection region with respect to the optical axis, and the substrate

transport system and the substrate stage are arranged in a divided space which is purged with inert gas, and a position detection system for detecting an alignment mark on the substrate. --